



P-Channel 60-V (D-S) MOSFET

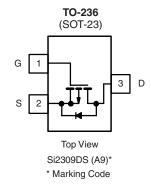
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 60	0.340 at V _{GS} = - 10 V	- 1.25		
	0.550 at V _{GS} = - 4.5 V	- 1		

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET



FREE



Ordering Information: Si2309DS-T1

Si2309DS-T1-E3 (Lead (Pb)-free)

Si2309DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	$I_A = 25$ °C, unles	ss otnerwise not	iea .		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 60	V	
Gate-Source Voltage		V _{GS}	± 20	v	
Openia	T _A = 25 °C	I-	- 1.25		
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 70 °C	I _D	- 0.85		
Pulsed Drain Current		I _{DM}	- 8	_ A	
Avalanche Current	L = 0.1 mH	I _{AS}	- 5		
Mariana Barra Birata di adh	T _A = 25 °C	Р	1.25	١٨/	
Maximum Power Dissipation ^{a, b}	T _A = 70 °C	P _D	0.8	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian Incation to Ambient	t ≤ 5 s	R _{thJA}		100	°C/W
Maximum Junction-to-Ambient ^a	Steady State		130	166	
Maximum Junction-to-Lead ^a	Steady State	R_{thJL}	45	60	

Notes

a. Surface Mounted on FR4 board.

b. t ≤ 5 s.

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.

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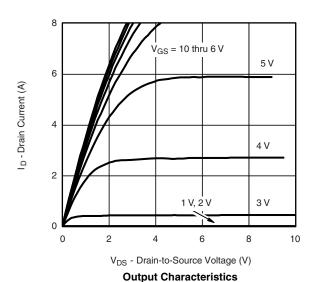
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{DS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	μΑ - 60			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	- 1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zara Cata Valtaga Drain Current		V _{DS} = - 48 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 48 V, V _{GS} = 0 V, T _J = 125 °C			- 50	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge -4.5 \text{ V}, V_{GS} = -10 \text{ V}$	- 6			Α	
Drain-Source On-State Resistance ^a	D	V _{GS} = - 10 V, I _D = - 1.25 A		0.275	0.340	Ω	
	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 1 A		0.406	0.550		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 4.5 V, I _D = - 1 A		1.9		S	
Dynamic ^b							
Total Gate Charge	Q_g			5.4	12	nC	
Gate-Source Charge	Q_{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -1.25 \text{ A}$		1.15			
Gate-Drain Charge	Q_{gd}			0.92			
Turn-On Delay Time	t _{d(on)}			10.5	20	ns	
Rise Time	t _r	V_{DD} = - 30 V, R_L = 30 Ω		11.5	20		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, V_{GEN} = - 4.5 V, R_G = 6 Ω		15.5	30		
Fall Time	t _f			7.5	15		
Source-Drain Rating Characteristics	b						
Continuous Current	I _S				- 1.25	Α	
Pulsed Current	I _{SM}				- 8	_ ^	
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.25 A, V _{GS} = 0 V		- 0.82	- 1.2	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.25 A, dI/dt = 100 A/μs		30	55	ns	

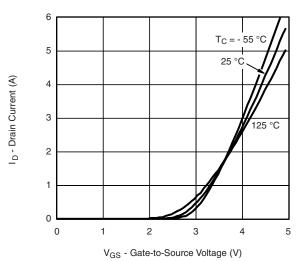
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



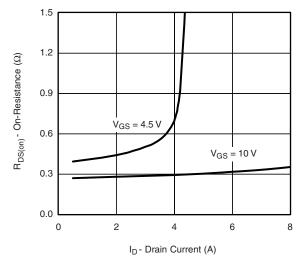




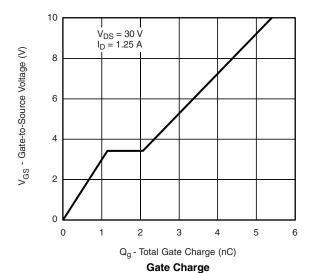


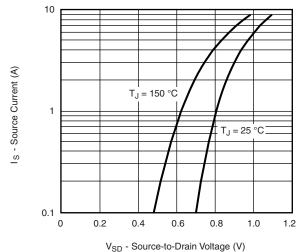


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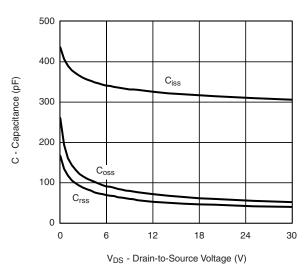


On-Resistance vs. Drain Current

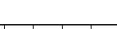


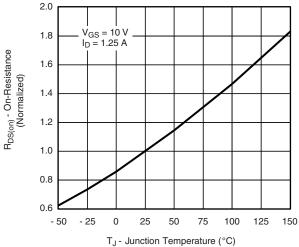


Source-Drain Diode Forward Voltage

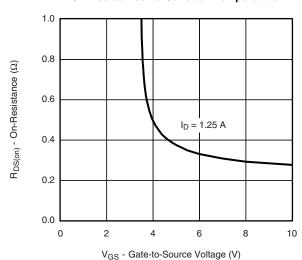


Capacitance





On-Resistance vs. Junction Temperature

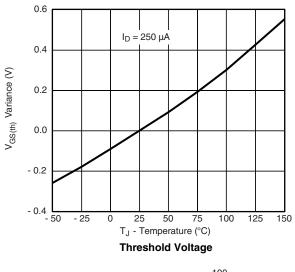


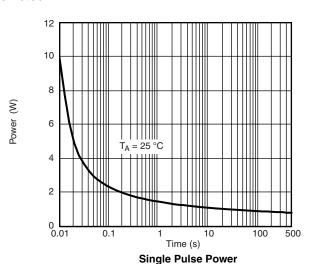
On-Resistance vs. Gate-to-Source Voltage

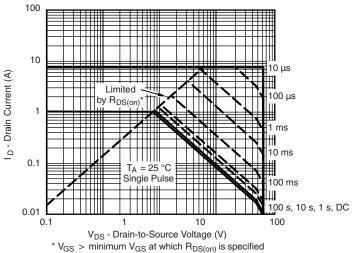
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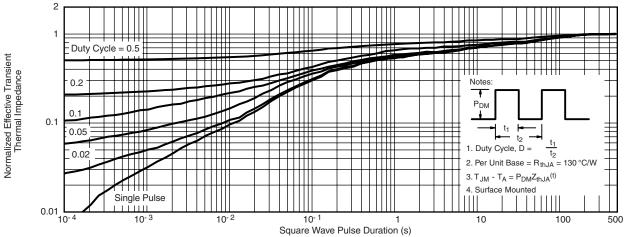
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

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